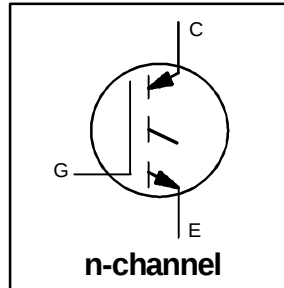


## Features

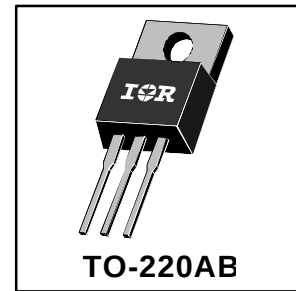
- Switching-loss rating includes all "tail" losses
- Optimized for high operating frequency (over 5kHz)  
See Fig. 1 for Current vs. Frequency curve



|                              |
|------------------------------|
| $V_{CES} = 600V$             |
| $V_{CE(sat)} \leq 3.0V$      |
| @ $V_{GE} = 15V, I_C = 6.5A$ |

## Description

Insulated Gate Bipolar Transistors (IGBTs) from International Rectifier have higher usable current densities than comparable bipolar transistors, while at the same time having simpler gate-drive requirements of the familiar power MOSFET. They provide substantial benefits to a host of high-voltage, high-current applications.



## Absolute Maximum Ratings

|                           | Parameter                                           | Max.                              | Units      |
|---------------------------|-----------------------------------------------------|-----------------------------------|------------|
| $V_{CES}$                 | Collector-to-Emitter Voltage                        | 600                               | V          |
| $I_C @ T_C = 25^\circ C$  | Continuous Collector Current                        | 13                                | A          |
| $I_C @ T_C = 100^\circ C$ | Continuous Collector Current                        | 6.5                               |            |
| $I_{CM}$                  | Pulsed Collector Current ①                          | 52                                |            |
| $I_{LM}$                  | Clamped Inductive Load Current ②                    | 52                                |            |
| $V_{GE}$                  | Gate-to-Emitter Voltage                             | $\pm 20$                          | V          |
| $E_{ARV}$                 | Reverse Voltage Avalanche Energy ③                  | 5                                 | mJ         |
| $P_D @ T_C = 25^\circ C$  | Maximum Power Dissipation                           | 60                                | W          |
| $P_D @ T_C = 100^\circ C$ | Maximum Power Dissipation                           | 24                                |            |
| $T_J$<br>$T_{STG}$        | Operating Junction and<br>Storage Temperature Range | -55 to +150                       | $^\circ C$ |
|                           | Soldering Temperature, for 10 sec.                  | 300 (0.063 in. (1.6mm) from case) |            |
|                           | Mounting torque, 6-32 or M3 screw.                  | 10 lbf•in (1.1N•m)                |            |

## Thermal Resistance

|                 | Parameter                                 | Min. | Typ.       | Max. | Units        |
|-----------------|-------------------------------------------|------|------------|------|--------------|
| $R_{\theta JC}$ | Junction-to-Case                          | —    | —          | 2.1  | $^\circ C/W$ |
| $R_{\theta CS}$ | Case-to-Sink, flat, greased surface       | —    | 0.50       | —    |              |
| $R_{\theta JA}$ | Junction-to-Ambient, typical socket mount | —    | —          | 80   |              |
| Wt              | Weight                                    | —    | 2.0 (0.07) | —    | g (oz)       |

**Electrical Characteristics @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)**

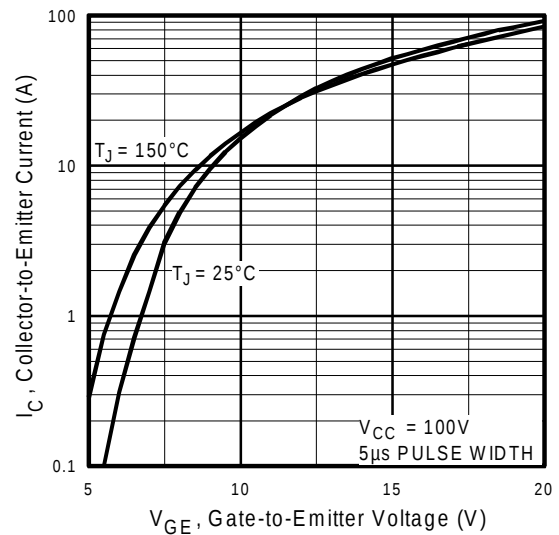
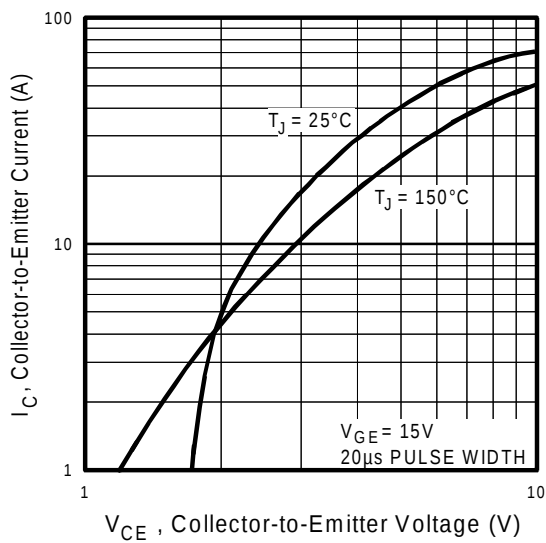
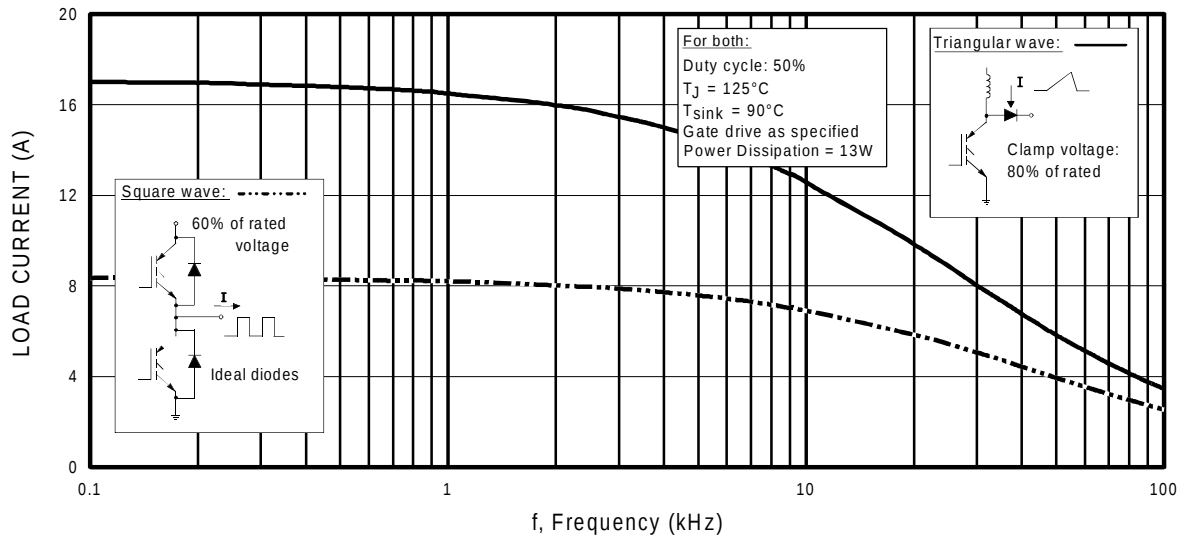
|                                 | Parameter                                | Min. | Typ. | Max.      | Units                | Conditions                                            |
|---------------------------------|------------------------------------------|------|------|-----------|----------------------|-------------------------------------------------------|
| $V_{(BR)CES}$                   | Collector-to-Emitter Breakdown Voltage   | 600  | —    | —         | V                    | $V_{GE} = 0V, I_C = 250\mu A$                         |
| $V_{(BR)ECS}$                   | Emitter-to-Collector Breakdown Voltage ④ | 20   | —    | —         | V                    | $V_{GE} = 0V, I_C = 1.0A$                             |
| $\Delta V_{(BR)CES}/\Delta T_J$ | Temperature Coeff. of Breakdown Voltage  | —    | 0.69 | —         | V/ $^\circ\text{C}$  | $V_{GE} = 0V, I_C = 1.0mA$                            |
| $V_{CE(on)}$                    | Collector-to-Emitter Saturation Voltage  | —    | 2.2  | 3.0       | V                    | $I_C = 6.5A$                                          |
|                                 |                                          | —    | 2.8  | —         |                      | $I_C = 13A$                                           |
|                                 |                                          | —    | 2.5  | —         |                      | $I_C = 6.5A, T_J = 150^\circ\text{C}$                 |
| $V_{GE(th)}$                    | Gate Threshold Voltage                   | 3.0  | —    | 5.5       |                      | $V_{CE} = V_{GE}, I_C = 250\mu A$                     |
| $\Delta V_{GE(th)}/\Delta T_J$  | Temperature Coeff. of Threshold Voltage  | —    | -11  | —         | mV/ $^\circ\text{C}$ | $V_{CE} = V_{GE}, I_C = 250\mu A$                     |
| $g_{fe}$                        | Forward Transconductance ⑤               | 1.4  | 4.3  | —         | S                    | $V_{CE} = 100V, I_C = 6.5A$                           |
| $I_{CES}$                       | Zero Gate Voltage Collector Current      | —    | —    | 250       | $\mu A$              | $V_{GE} = 0V, V_{CE} = 600V$                          |
|                                 |                                          | —    | —    | 1000      |                      | $V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$ |
| $I_{GES}$                       | Gate-to-Emitter Leakage Current          | —    | —    | $\pm 100$ | nA                   | $V_{GE} = \pm 20V$                                    |

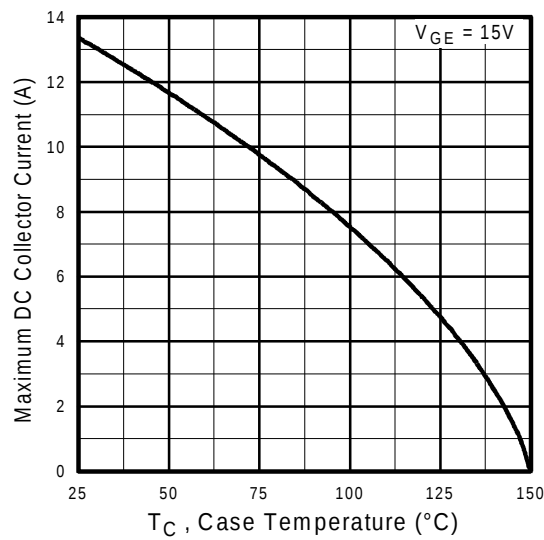
**Switching Characteristics @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)**

|              | Parameter                         | Min. | Typ. | Max. | Units | Conditions                     |
|--------------|-----------------------------------|------|------|------|-------|--------------------------------|
| $Q_g$        | Total Gate Charge (turn-on)       | —    | 16   | 22   | nC    | $I_C = 6.5A$                   |
| $Q_{ge}$     | Gate - Emitter Charge (turn-on)   | —    | 2.5  | 3.8  |       | $V_{CC} = 400V$                |
| $Q_{gc}$     | Gate - Collector Charge (turn-on) | —    | 7.8  | 13   |       | $V_{GE} = 15V$                 |
| $t_{d(on)}$  | Turn-On Delay Time                | —    | 22   | —    | ns    | $T_J = 25^\circ\text{C}$       |
| $t_r$        | Rise Time                         | —    | 12   | —    |       | $I_C = 6.5A, V_{CC} = 480V$    |
| $t_{d(off)}$ | Turn-Off Delay Time               | —    | 71   | 95   |       | $V_{GE} = 15V, R_G = 50\Omega$ |
| $t_f$        | Fall Time                         | —    | 91   | 280  |       | Energy losses include "tail"   |
| $E_{on}$     | Turn-On Switching Loss            | —    | 0.11 | —    | mJ    | See Fig. 9, 10, 11, 14         |
| $E_{off}$    | Turn-Off Switching Loss           | —    | 0.14 | —    |       |                                |
| $E_{ts}$     | Total Switching Loss              | —    | 0.25 | 0.50 |       |                                |
| $t_{d(on)}$  | Turn-On Delay Time                | —    | 23   | —    | ns    | $T_J = 150^\circ\text{C},$     |
| $t_r$        | Rise Time                         | —    | 13   | —    |       | $I_C = 6.5A, V_{CC} = 480V$    |
| $t_{d(off)}$ | Turn-Off Delay Time               | —    | 140  | —    |       | $V_{GE} = 15V, R_G = 50\Omega$ |
| $t_f$        | Fall Time                         | —    | 200  | —    |       | Energy losses include "tail"   |
| $E_{ts}$     | Total Switching Loss              | —    | 0.45 | —    | mJ    | See Fig. 10, 14                |
| $L_E$        | Internal Emitter Inductance       | —    | 7.5  | —    | nH    | Measured 5mm from package      |
| $C_{ies}$    | Input Capacitance                 | —    | 330  | —    | pF    | $V_{GE} = 0V$                  |
| $C_{oes}$    | Output Capacitance                | —    | 65   | —    |       | $V_{CC} = 30V$                 |
| $C_{res}$    | Reverse Transfer Capacitance      | —    | 6.0  | —    |       | $f = 1.0MHz$                   |

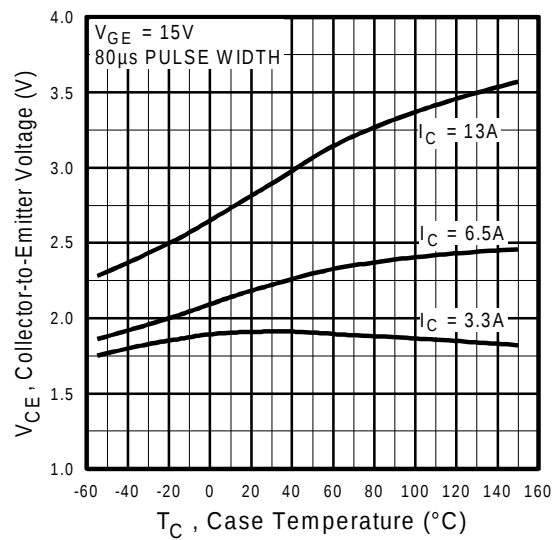
**Notes:**

- ① Repetitive rating;  $V_{GE}=20V$ , pulse width limited by max. junction temperature. ( See fig. 13b )
- ②  $V_{CC}=80\%(V_{CES}), V_{GE}=20V, L=10\mu H, R_G=50\Omega$ , ( See fig. 13a )
- ③ Repetitive rating; pulse width limited by maximum junction temperature.
- ④ Pulse width  $\leq 80\mu s$ ; duty factor  $\leq 0.1\%$ .
- ⑤ Pulse width  $5.0\mu s$ , single shot.

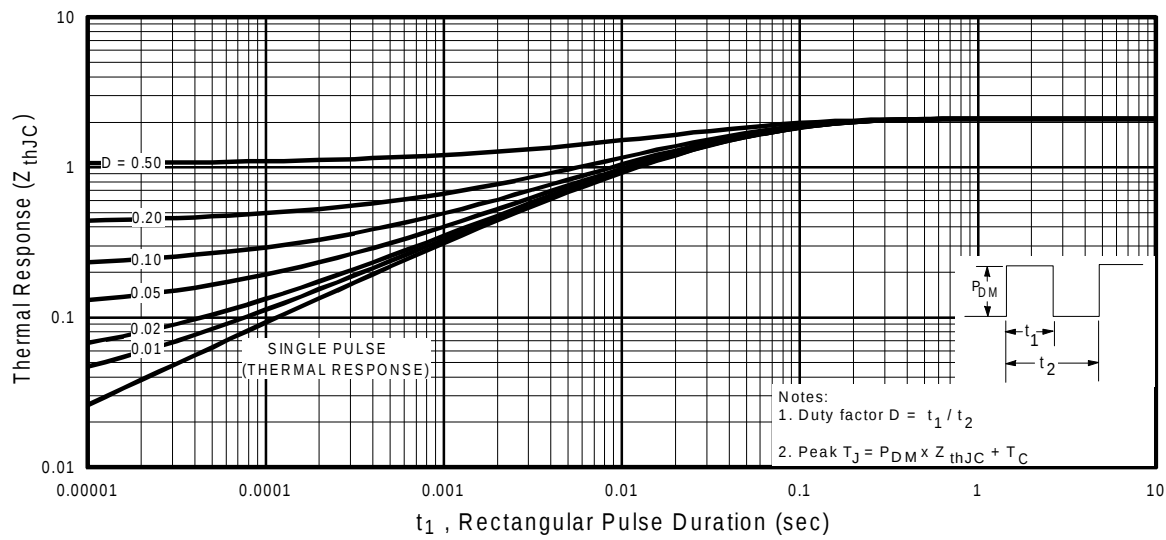




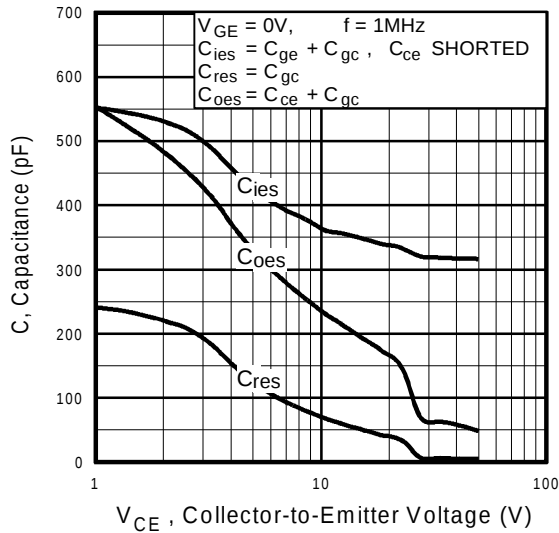
**Fig. 4 - Maximum Collector Current vs. Case Temperature**



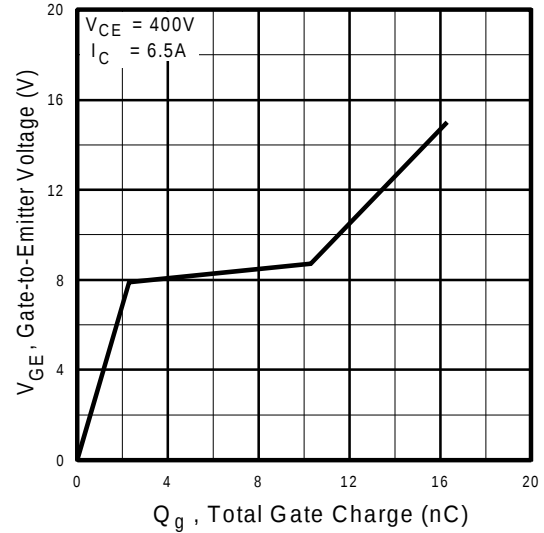
**Fig. 5 - Collector-to-Emitter Voltage vs. Case Temperature**



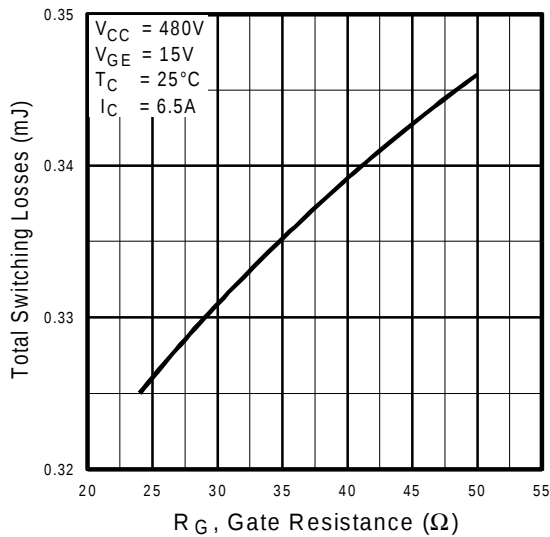
**Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case**



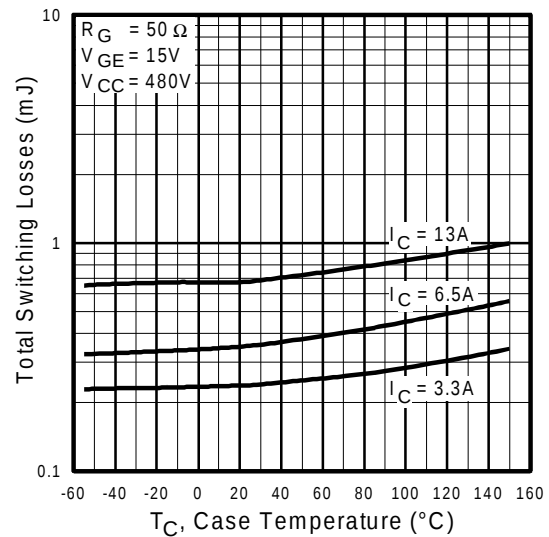
**Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage**



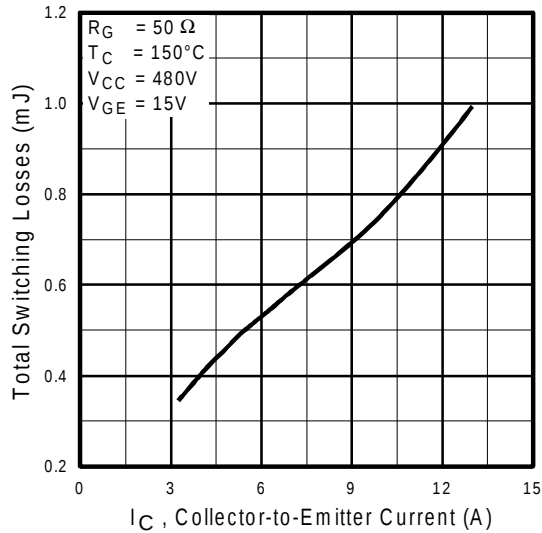
**Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage**



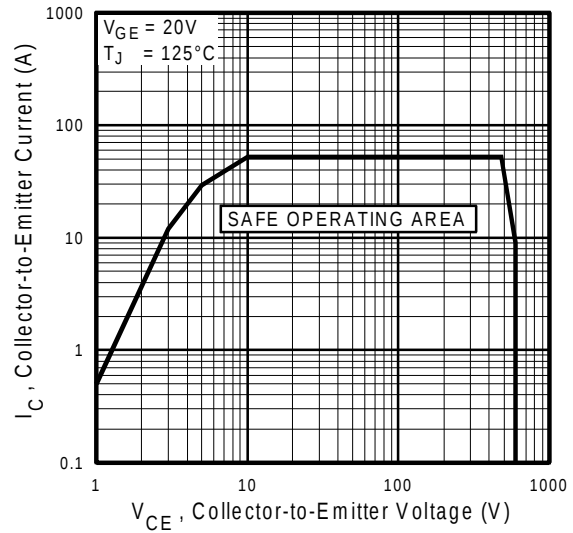
**Fig. 9 - Typical Switching Losses vs. Gate Resistance**



**Fig. 10 - Typical Switching Losses vs. Case Temperature**



**Fig. 11** - Typical Switching Losses vs. Collector-to-Emitter Current



**Fig. 12** - Turn-Off SOA

Refer to Section D for the following:

**Appendix C: Section D - page D-5**

Fig. 13a - Clamped Inductive Load Test Circuit

Fig. 13b - Pulsed Collector Current Test Circuit

Fig. 14a - Switching Loss Test Circuit

Fig. 14b - Switching Loss Waveform

Package Outline 1 - JEDEC Outline TO-220AB

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